onsemi

Silicon Carbide (SiC) Diode -EliteSiC, TO247-2, 25 A, **1700 V SiC Merged PiN-Schottky (MPS) Diode**

UJ3D1725K2

Description

onsemi offers the 3rd generation of high performance SiC Merged-PiN-Schottky (MPS) diodes. With zero reverse recovery charge and 175 °C maximum junction temperature, these diodes are ideally suited for high frequency and high efficiency power systems with minimum cooling requirements.

Features

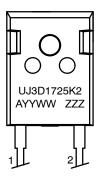
- Maximum Operating Temperature of 175 °C
- Easy Paralleling
- Extremely Fast Switching not Dependent on Temperature
- No Reverse or Forward Recovery
- Enhanced Surge Current Capability, MPS Structure
- 100% UIS Tested
- This Device is Halogen Free and RoHS Compliant with Exemption 7a, Pb-Free 2LI (on second level interconnection)

Typical Applications

- Power Converters
- Industrial Motor Drives
- Switch Mode Power Supplies
- Power Factor Correction Modules



MARKING DIAGRAM



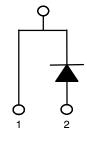
| UJ3D1725K2 | = Spec |
|------------|----------|
| A | = Asse |
| YY | = Year |
| WW | = Work |
| ZZZ | = Lot IE |
| | |

cific Device Code mbly Location

| = | Year | |
|---|------|--|

- k Week
- D

PIN CONNECTIONS



ORDERING INFORMATION

See detailed ordering and shipping information on page 4 of this data sheet.

DATA SHEET www.onsemi.com

UJ3D1725K2

MAXIMUM RATINGS

| Parameter | Symbol | Test Conditions | Value | Unit |
|---|-----------------------------------|---|------------|------------------|
| DC Blocking Voltage | V _R | | 1700 | V |
| Repetitive Peak Reverse Voltage, T_J = 25 °C | V _{RRM} | | 1700 | V |
| Surge Peak Reverse Voltage | V _{RSM} | | 1700 | V |
| Maximum DC Forward Current | ١ _F | T _C = 138 °C | 25 | А |
| Non-repetitive Forward Surge Current Sine | I _{FSM} | T_{C} = 25 °C, t_{p} = 10 ms | 180 | А |
| Halfwave | | $T_{C} = 110 \ ^{\circ}C, t_{p} = 10 \ ms$ | 163 | |
| Repetitive Forward Surge Current Sine | I _{FRM} | T_{C} = 25 °C, t_{p} = 10 ms | 117 | А |
| Halfwave, D = 0.1 | | $T_{C} = 110 \ ^{\circ}C, t_{p} = 10 \ ms$ | 68.7 | |
| Non-repetitive Peak Forward Current | I _{F, max} | T _C = 25 °C, t _p = 10 μs | 1100 | А |
| | | T _C = 110 °C, t _p = 10 μs | 1100 | |
| i ² t Value | ∫i ² dt | T_{C} = 25 °C, t_{p} = 10 ms | 162 | A ² s |
| | | $T_{C} = 110 \ ^{\circ}C, t_{p} = 10 \ ms$ | 133 | 7 |
| Power Dissipation | P _{tot} | T _C = 25 °C | 283 | W |
| | | T _C = 138 °C | 69.8 | |
| Maximum Junction Temperature | T _{J, max} | | 175 | °C |
| Operating and Storage Temperature | T _J , T _{STG} | | –55 to 175 | °C |
| Soldering Temperatures, Wavesoldering only Allowed at Leads | T _{sold} | 1.6 mm from case for 10 s | 260 | °C |

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

| Parameter | Symbol | Test Conditions | Min | Тур | Мах | Unit |
|--------------------------------------|----------------|-----------------|-----|------|------|------|
| Thermal Resistance, Junction-to-Case | R_{\thetaJC} | | 1 | 0.41 | 0.53 | °C/W |

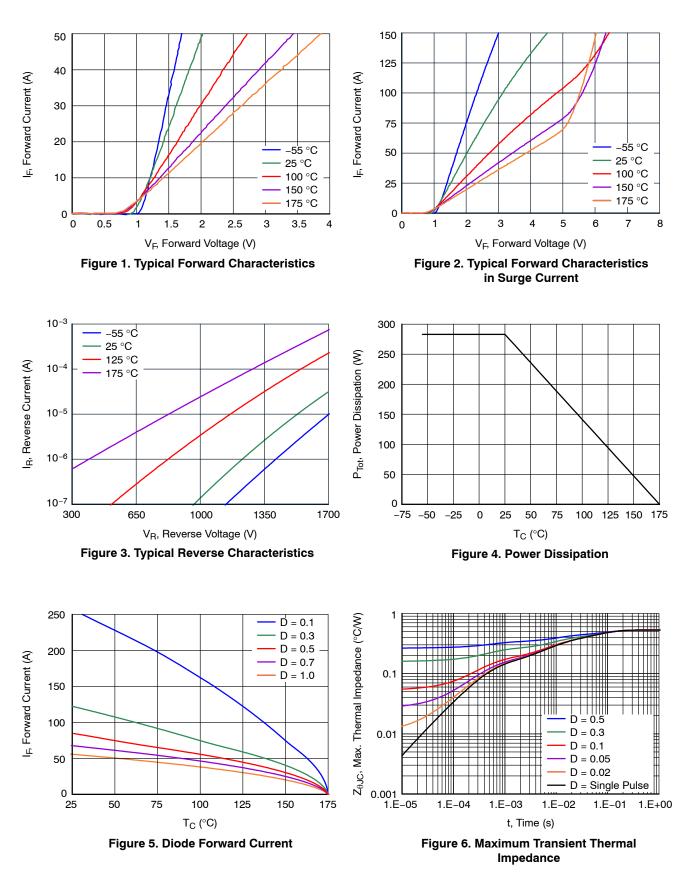
ELECTRICAL CHARACTERISTICS (T_J = +25 °C unless otherwise specified)

| Parameter | Symbol | Test Conditions | Min | Тур | Max | Unit |
|----------------------------------|----------------|--|-----|------|------|------|
| Forward Voltage | V _F | I _F = 25 A, T _J = 25 °C | - | 1.54 | 1.7 | V |
| | | I _F = 25 A, T _J = 150 °C | - | 2.1 | - | |
| | | l _F = 25 A, T _J = 175 °C | - | 2.3 | 2.75 | |
| Reverse Current | I _R | V_R = 1700 V, T_J = 25 °C | - | 24 | 360 | μΑ |
| | | V_{R} = 1700 V, T_{J} = 175 °C | - | 950 | - | |
| Total Capacitive Charge (Note 1) | Q _C | V _R = 1200 V | - | 184 | - | nC |
| Total Capacitance | С | V _R = 1 V, f = 1 MHz | - | 1500 | - | pF |
| | | V _R = 800 V, f = 1 MHz | - | 100 | - | |
| | | V _R = 1700 V, f = 1 MHz | - | 80 | - | 1 |
| Capacitance Stored Energy | E _C | V _R = 1200 V | - | 78 | - | μJ |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 1. Q_C is independent on T_J, di_F/dt, and I_F as shown in the application note <u>AND90316/D</u>

UJ3D1725K2

TYPICAL PERFORMANCE DIAGRAMS



UJ3D1725K2

TYPICAL PERFORMANCE DIAGRAMS (continued)

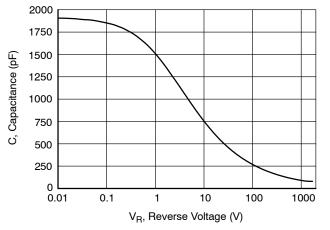
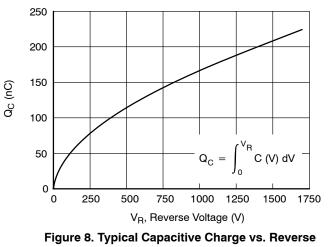


Figure 7. Capacitance vs. Reverse Voltage at 1 MHz



. Voltage

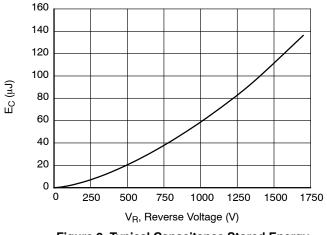
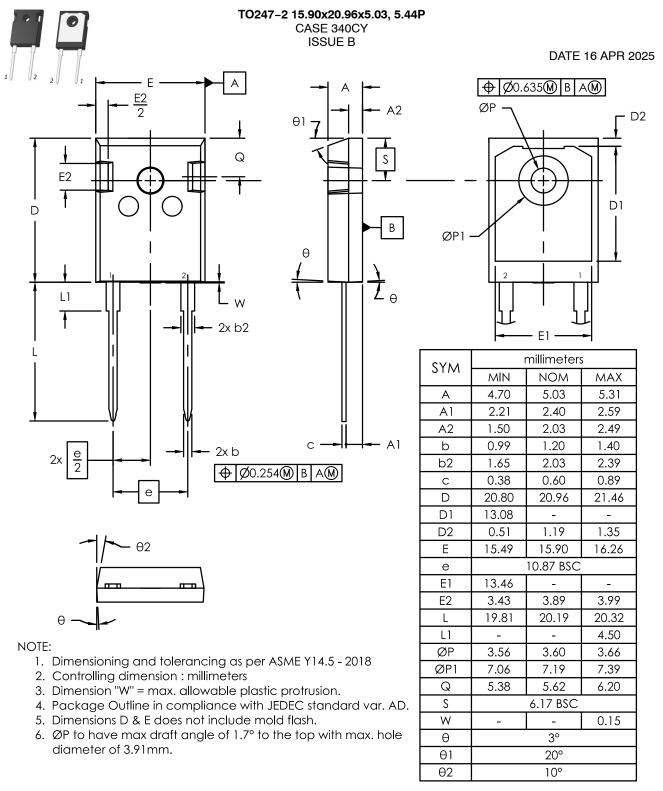


Figure 9. Typical Capacitance Stored Energy vs. Reverse Voltage

ORDERING INFORMATION

| Part Number | Marking | Package | Shipping |
|-------------|------------|------------------------------------|------------------|
| UJ3D1725K2 | UJ3D1725K2 | TO247-2 (Pb-Free, Halogen Free) | 600 Units / Tube |

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|------------------|---------------------------------|---|-------------|--|
| DESCRIPTION: | TO247-2 15.90x20.96x5.03, 5.44P | | PAGE 1 OF 1 | |

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